

MA3XD17

Silicon epitaxial planar type

For rectification

For protection against reverse current

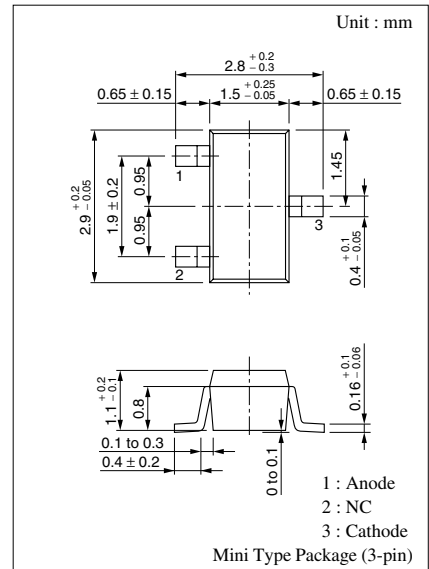
■ Features

- Mini type 3-pin package
- High breakdown voltage $V_R = 100$ V

■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

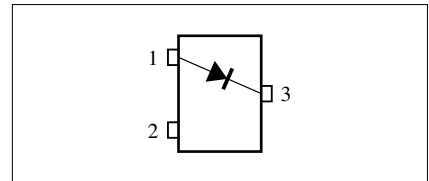
Parameter	Symbol	Rating	Unit
Reverse voltage (DC)	V_R	100	V
Peak reverse voltage	V_{RM}	100	V
Non-repetitive peak forward surge current*	I_{FSM}	1.5	A
Average forward current	$I_{F(AV)}$	300	mA
Junction temperature	T_j	125	$^\circ\text{C}$
Storage temperature	T_{stg}	-55 to +150	$^\circ\text{C}$

Note) * : The peak-to-peak value in one cycle of 50 Hz sine-wave (non-repetitive)



Marking Symbol: M5K

Internal Connection



■ Electrical Characteristics $T_a = 25^\circ\text{C} \pm 3^\circ\text{C}$

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Reverse current (DC)	I_R	$V_R = 100$ V			200	μA
Forward voltage (DC)	V_F	$I_F = 300$ mA		0.50	0.58	V
Terminal capacitance	C_t	$V_R = 0$ V, $f = 1$ MHz		100		pF
Reverse recovery time*	t_{rr}	$I_F = I_R = 100$ mA $I_{rr} = 0.1 \cdot I_R$, $R_L = 100$ Ω		7		ns

Note) 1. Schottky barrier diode is sensitive to electric shock (static electricity, etc.). Due attention must be paid on the charge of a human body and the leakage of current from the operating equipment.

1. Rated input/output frequency: 250 MHz
3. *: t_{rr} measuring circuit

